Product data sheet

1. General description

Silicon Carbide Schottky diode in a SOD59A (TO-220AC) plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom/Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED/OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	650	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} \leq 136 °C; square-wave pulse; Fig. 1; Fig. 2		-	-	4	Α
T _j	junction temperature			-	-	175	°C
Static characteristics							
V _F	forward voltage	I _F = 4 A; T _j = 25 °C; <u>Fig. 4</u>		-	1.5	1.7	V





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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Dynamic characteristics							
Q _r	recovered charge	$I_F = 4 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$;		-	7	-	nC
		T _j = 25 °C; <u>Fig. 5</u>					

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	7 0 5	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59A)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NXPSC04650	TO-220AC	Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59A

7. Marking

Table 4. Marking codes

Type number	Marking code
NXPSC04650	NXPSC04650

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	650	V
V_{RWM}	crest working reverse voltage		-	650	V
V_R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 136 °C; square-wave pulse; Fig. 1; Fig. 2	-	4	A
I _{FRM}	repetitive peak forward current	$\bar{\delta}$ = 0.5; t_p = 25 µs; T_{mb} ≤ 136 °C; square-wave pulse	-	8	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	24	A
		t_p = 10 μ s; $T_{j(init)}$ = 25 °C; square-wave pulse	-	235	A
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-	175	°C

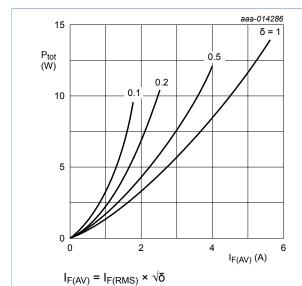


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

 V_o = 1.260 V; R_s = 0.211 Ω

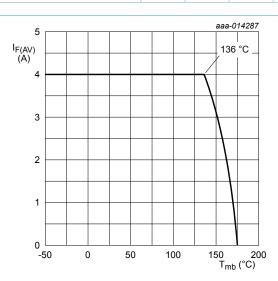


Fig. 2. Forward current as a function of mounting base temperature; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 3	-	-	3.3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

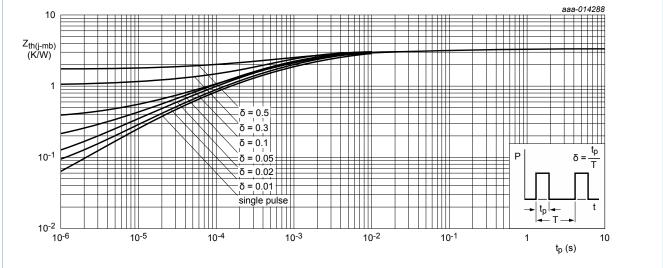


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

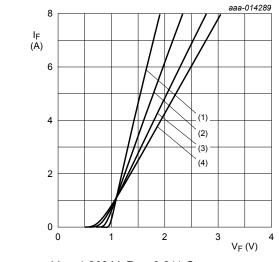
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics		'			
V _F	forward voltage	I _F = 4 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.5	1.7	V
		I _F = 4 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.8	2.1	V
I _R rever	reverse current	V _R = 650 V; T _j = 25 °C	-	-	170	μΑ
		V _R = 650 V; T _j = 150 °C	-	-	550	μΑ
Dynamic c	haracteristics		'			
Q _r	recovered charge	$I_F = 4 \text{ A}; dI_F/dt = 500 \text{ A/}\mu\text{s}; V_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 5}}{\text{C}}$	-	7	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	130	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	16	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	13	-	pF



 V_o = 1.260 V; R_s = 0.211 Ω

(1) T_i = 25 °C; typical values

(2) T_i = 100 °C; typical values

(3) $T_j = 150$ °C; typical values

(4) T_i = 175 °C; typical values



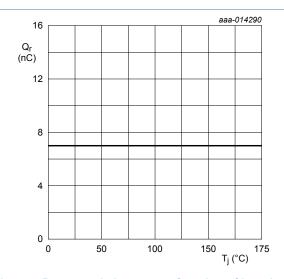
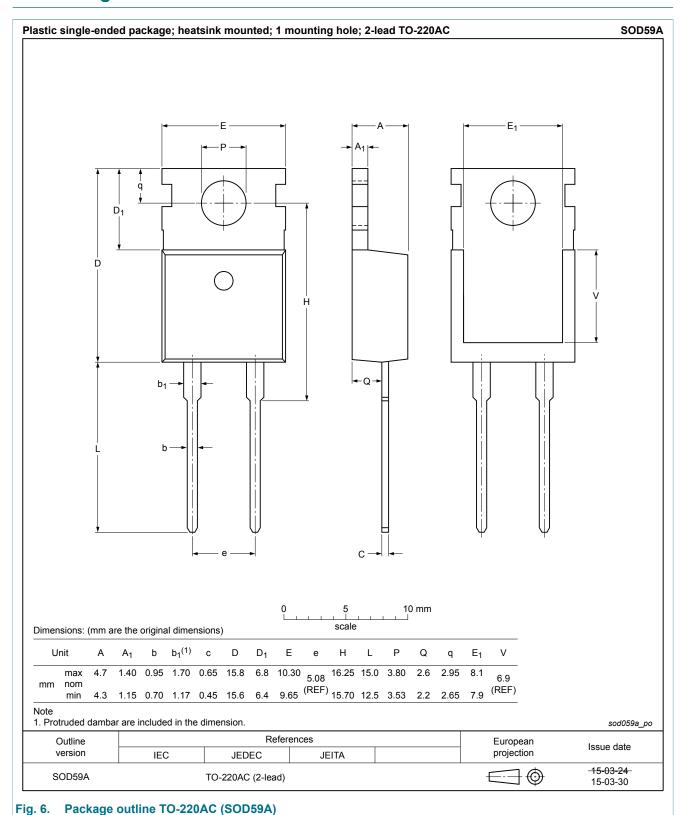


Fig. 5. Recovered charge as a function of junction temperature

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11. Package outline



Product data sheet

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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